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Web Results 1 - 6 of about 9 for power mosfet and vertical and source and drain and drift and trenches and

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Patent 6054752: Semiconductor device

A **source** region 804 is formed further around the **trench** 807, thus completing a ... Next, a method for manufacturing the **vertical power MOSFET** shown in FIG. ...

www.freepatentsonline.com/6054752.html - [Similar pages](#)

BT High-breakdown-voltage semiconductor device Number:6855970 from ...

a **second electrode** filling each of the plurality of first **trenches** and in ... **drift** layer. **Source**, gate, and **drain** electrodes are disposed in the n.sup. ...

www.banner-trader.com/Patents/High_breakdown_voltage_semiconductor_6855970.html - 69k - [Cached](#) - [Similar pages](#)

MOS type semiconductor device - US Patent 5079607

... To satisfy these demands, a **vertical type power MOSFET**, in ... view of the essential part of the **power MOSFET** of an ... The n + region 15 is a **source** region and n ...

www.patentstorm.us/patents/5079607.html - 36k - Supplemental Result - [Cached](#) - [Similar pages](#)

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... gate bipolar transistor used as a **power** switching device with ... transistor 111 **source** electrode 113 gate electrode 117 ... of surface region of **drift** layer, emitter ...

thomsonscientific.jp/products/itp/pdf/disc/itdedis01.pdf - Supplemental Result - [Cached](#) - [Similar pages](#)

High-voltage semiconductor component US Patent 6630698

... Milestone Toward a New **Power MOSFET** Generation" featured in ... Article "**Power Semiconductors Proliferate**" published in Electronics ... a line running **vertical** to the ...

patents.nimblewisdom.com/patent/6630698-High-voltage-semiconductor-component - 79k - Supplemental Result - [Cached](#) - [Similar pages](#)

Silicon carbide semiconductor device with trench US Patent 6020600

... The **vertical power MOSFET** shown in FIG ... 34 is provided more inward than the n.sup.+ type **drain** region 33 ... An n.sup.+ type **source** region 35 is provided on a second ...

patents.nimblewisdom.com/patent/6020600-Silicon-carbide-semiconductor-device-with-trench - 78k

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